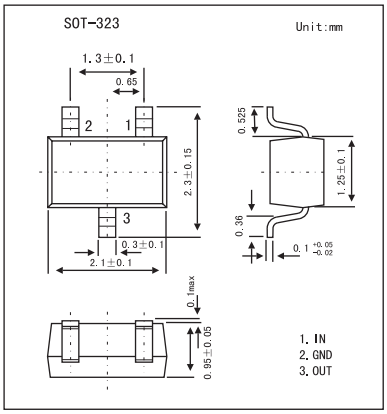
Schottky barrier diode

1PS70SB20



■ Features

- Ultra high switching speed
- Low forward voltage
- Guard ring protected
- Small SMD plastic package.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			40	V
Continuous forward current	I_F			500	mA
Non-repetitive peak forward current	I_{FSM}	t = 8.3 ms half sine wave;JEDEC method		2	A
Storage temperature	T_{stg}		-65	+150	℃
Junction temperature	T_j			125	℃
thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$			500	K/W

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Forward voltage	V_F	I_F = 500 mA		550	mV
Reverse current	I_R	V_R = 35 V		100	μ A
		V_R = 35 V; T_j = 100 ℃;Note 1		10	mA
Diode capacitance	C_d	f = 1 MHz; V_R = 0;	60	90	pF

Note

1. Pulse test: t_p < 300 μ s; δ ≤ 0.02.
2. Refer to SOT323(SC-70) Standard mounting conditions.

■ Marking

Marking	72